



TO-252-2 Plastic-Encapsulated Transistors

2SD1758 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 2 A

Collector-base voltage

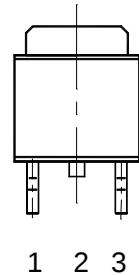
$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-252-2

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=500mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A, I_B=0.2A$			0.8	V
Transition frequency	f_T	$V_{CE}=5V, I_E=50mA, f=100MHz$	80			MHz